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(54) Title: CURRENT SHARING MISMATCH AND SWITCHING OSCILLATION REDUCTION IN POWER SEMICONDUCTOR DEVICE MODULES

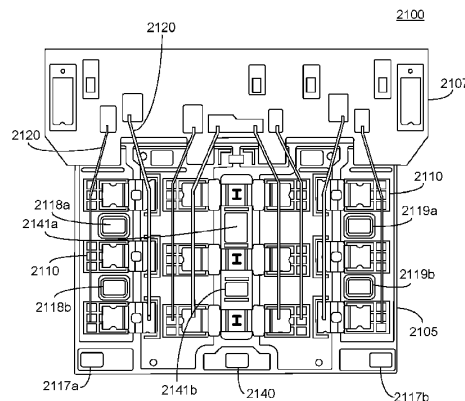


FIG. 21

(57) Abstract: In a general aspect, a half-bridge power module (800) includes a substrate (505) having a plurality of patterned metal layers (517a, 530a, 540) disposed thereon. The module also includes respective pluralities of high-side and low-side transistors (510, 520) disposed on the metal layers. A plurality of conductive clips (532, 542) respectively electrically couple the high-side transistors and the low-side transistors with the metal layers. ADC+ terminal (815a), a DC- terminal (825) and an output terminal (835) of the half-bridge module are also respectively, electrically coupled with the plurality of patterned metal layers.

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WO 2024/086851 A2

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